

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	50mΩ @V _{GS} = -4.5V	-4.5A
	100mΩ @V _{GS} = -2.5V	-3.2A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

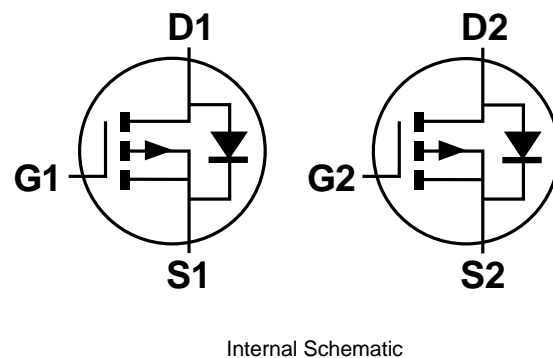
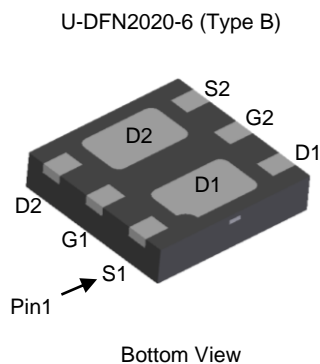
Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208④
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



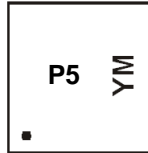
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2065UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2065UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

Site 1

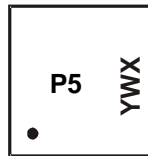


P5 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2016	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D	...	H	I	J	K	L	M	N	O	P	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



P5 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 0 = 2020)
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	...	0	1	2	3	4	5	6	7	8	9
Week	1-26			27-52				53				
Code	A-Z			a-z				z				
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C	I _D	-4.5	A
		T _A = +85°C		-3.6	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-25	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-1.4	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-13	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	9	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	171	°C/W
	t < 10s		131	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.54	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	82	°C/W
	t < 10s		60	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	13	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	µA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	40	50	mΩ	V _{GS} = -4.5V, I _D = -2.0A
			55	100		V _{GS} = -2.5V, I _D = -2.0A
			75	150		V _{GS} = -1.8V, I _D = -1.6A
			95	200		V _{GS} = -1.5V, I _D = -1.0A
			—	—		V _{GS} = 0V, I _S = -1A
Diode Forward Voltage	V _{SD}	—	-0.75	-1.1	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	752	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	87	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	78	—	pF	
Gate Resistance	R _G	—	15.2	—	Ω	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	9.1	—	nC	V _{GS} = -4.5V, V _{DS} = -4V, I _D = -3.5A
Gate-Source Charge	Q _{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.9	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.4	—	ns	V _{DS} = -4V, V _{GS} = -4.5V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _R	—	8.3	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	47	—	ns	
Turn-Off Fall Time	t _F	—	20	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

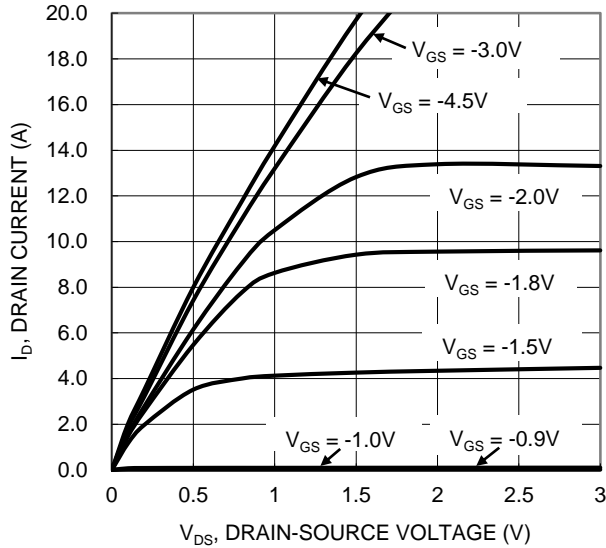


Figure 1. Typical Output Characteristic

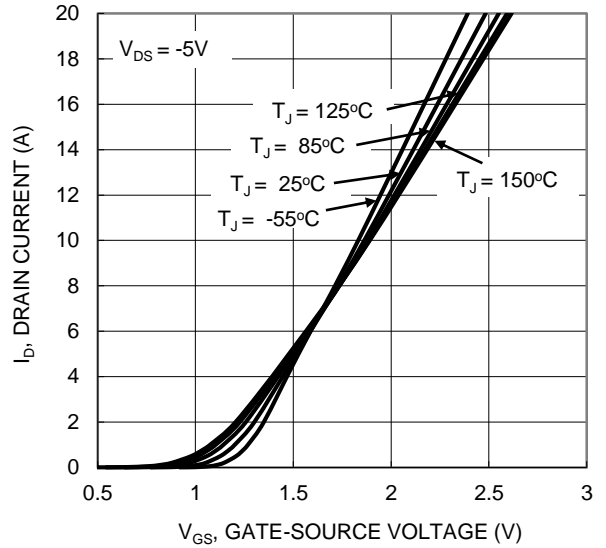


Figure 2. Typical Transfer Characteristic

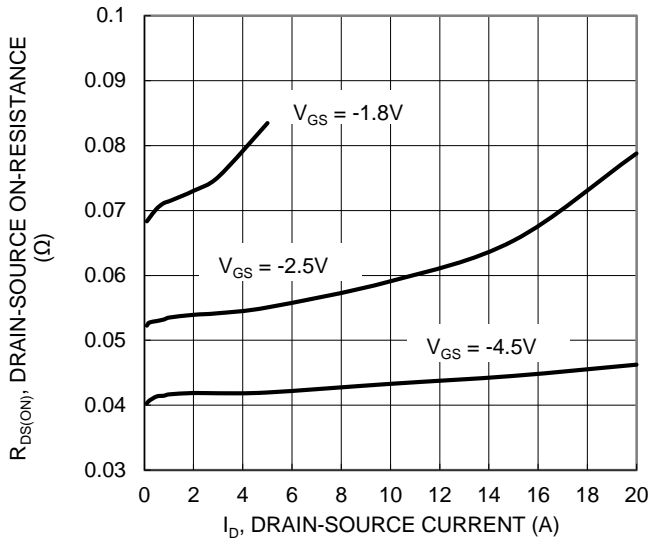


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

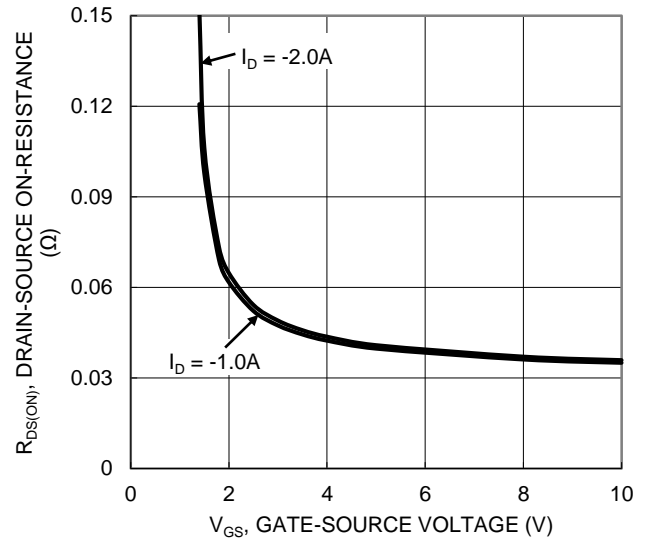


Figure 4. Typical Transfer Characteristic

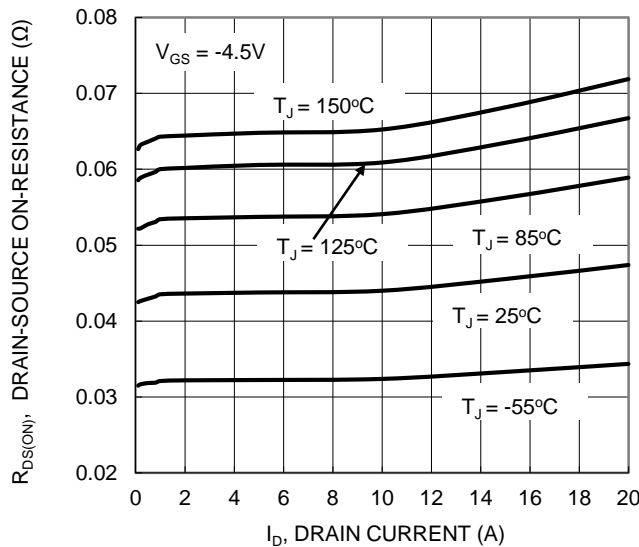


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

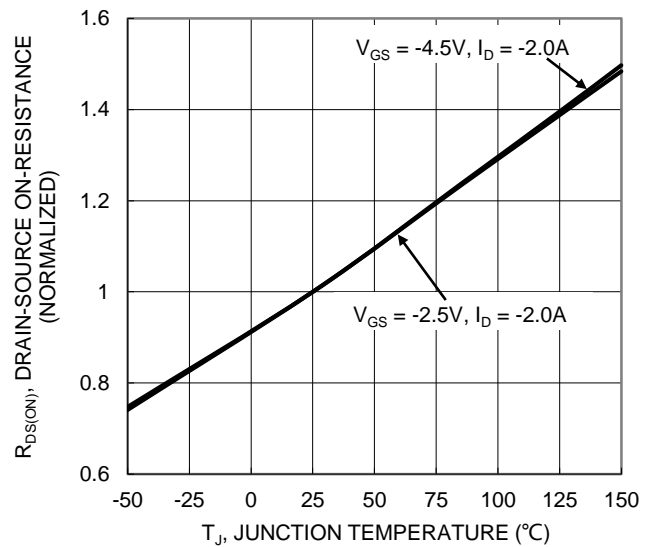
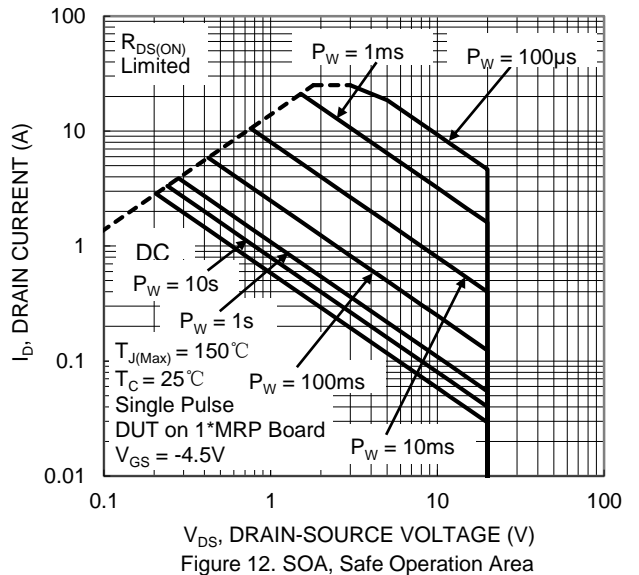
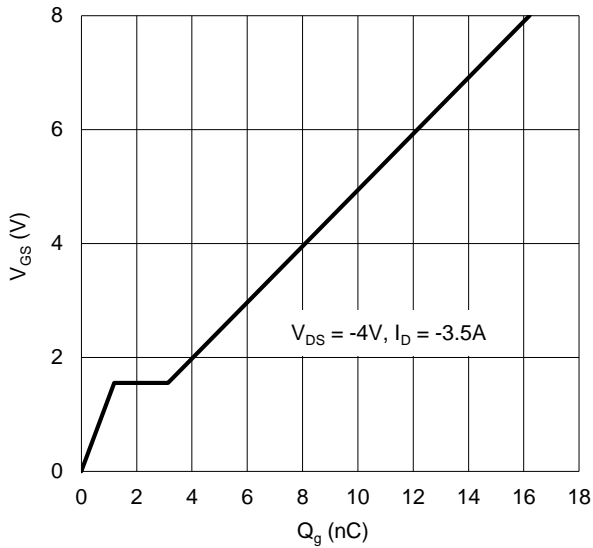
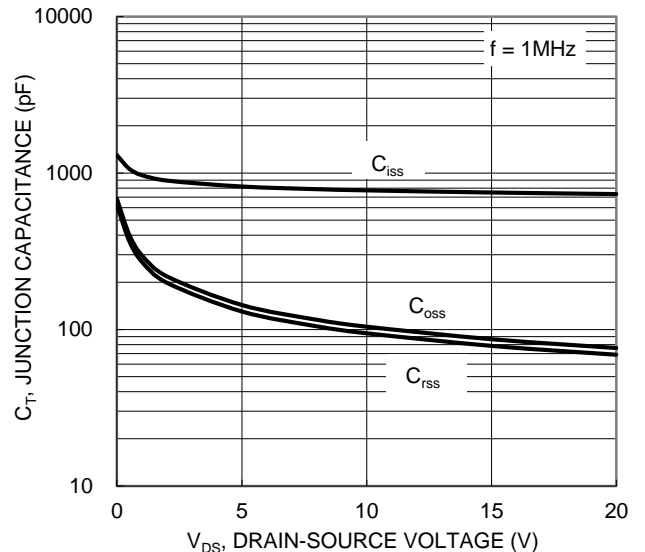
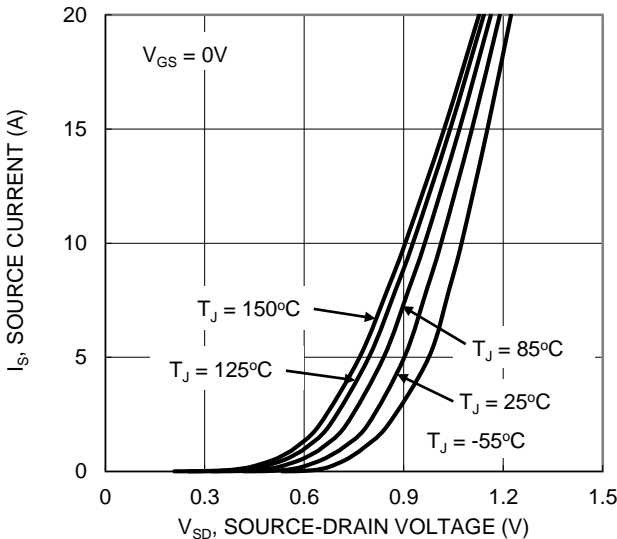
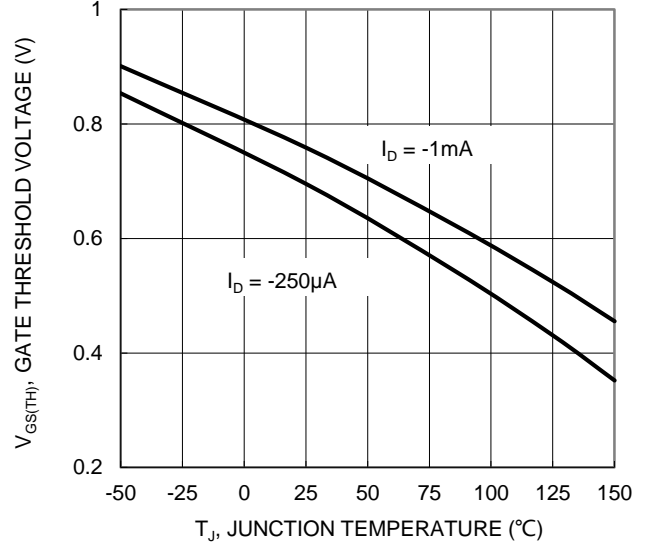
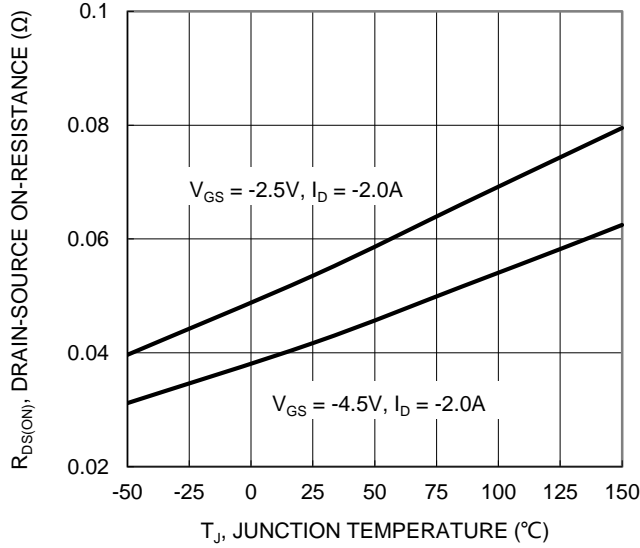


Figure 6. On-Resistance Variation with Junction Temperature



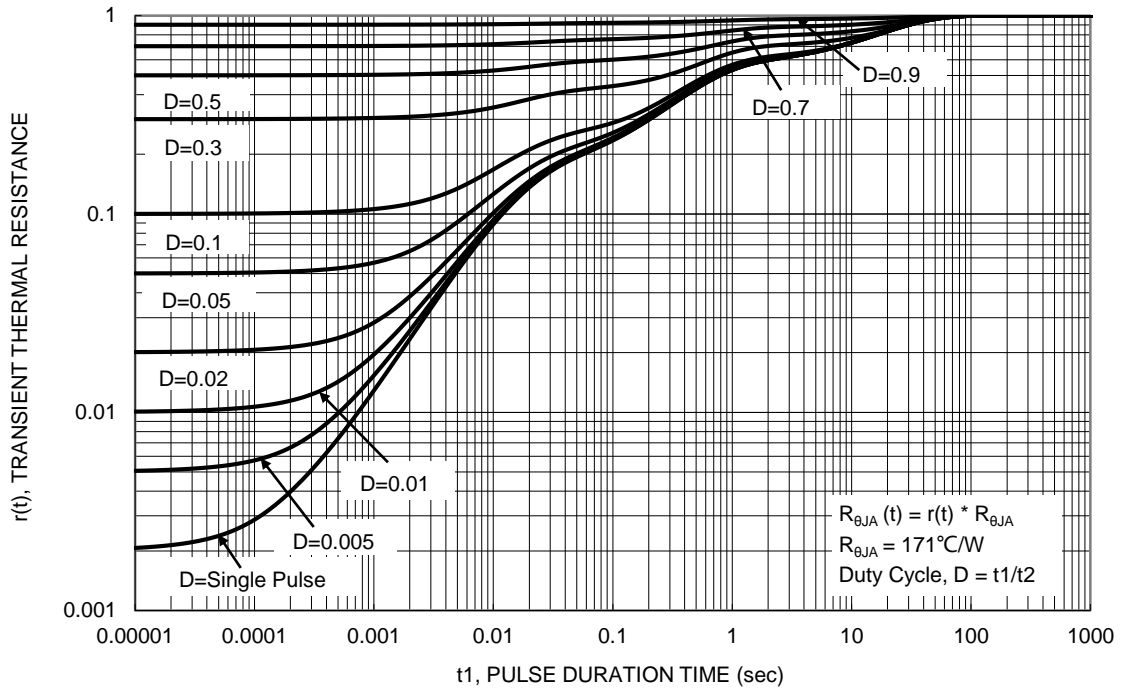
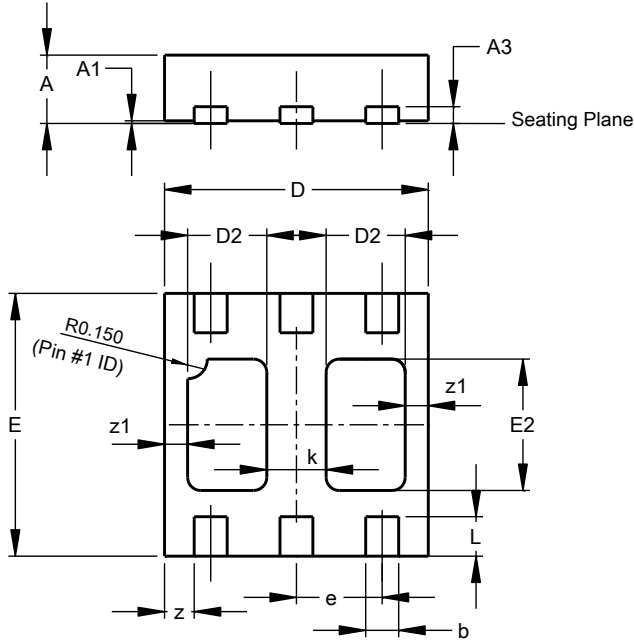


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)

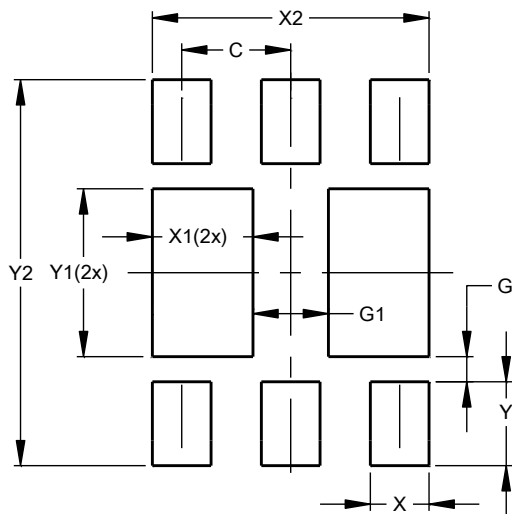


U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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